

2SC5080

Silicon NPN Epitaxial Transistor

Application

VHF & UHF wide band amplifire

Features

- High gain bandwidth product
 $f_T = 13.5$ GHz typ
- High gain, low noise figure
 $PG = 18$ dB typ,
 $NF = 1.1$ dB typ at $f = 900$ MHz

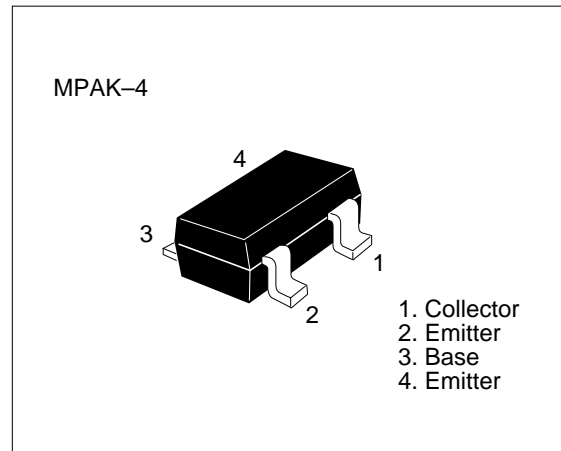


Table 1 Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

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Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 12 V, I_E = 0$
	I_{CEO}	—	—	1	mA	$V_{CE} = 9 V, R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 1.5 V, I_C = 0$
DC current transfer ratio	h_{FE}	50	90	160		$V_{CE} = 5 V, I_C = 20 mA$
Output capacitance	C_{ob}	—	0.4	0.75	pF	$V_{CB} = 5 V, I_E = 0, f = 1 MHz$
Gain bandwidth product	f_T	10.5	13.5	—	GHz	$V_{CE} = 5 V, I_C = 20 mA$
Power gain	PG	15	18	—	dB	$V_{CE} = 5 V, I_C = 20 mA, f = 900 MHz$
Noise figure	NF	—	1.1	2.0	dB	$V_{CE} = 5 V, I_C = 5 mA, f = 900 MHz$

Note: Marking of 2SC5080 is "ZD-".

Attention: This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.

Table 3 S Parameter ($V_{CE} = 5 \text{ V}$, $I_C = 5 \text{ mA}$, $Z_O = 50 \Omega$)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
200	0.798	-30.8	11.47	157.3	0.0329	73.0	0.936	-20.0
400	0.699	-60.8	9.88	139.6	0.0570	60.8	0.820	-35.1
600	0.592	-83.0	8.35	126.1	0.0718	53.0	0.703	-46.0
800	0.532	-99.9	7.03	115.7	0.0817	48.0	0.607	-54.0
1000	0.465	-114.5	6.02	107.6	0.0891	45.4	0.532	-59.8
1200	0.432	-128.2	5.23	101.0	0.0939	44.6	0.478	-64.3
1400	0.401	-139.6	4.58	95.2	0.0993	44.1	0.440	-67.7
1600	0.390	-150.2	4.14	90.7	0.103	44.8	0.405	-71.6
1800	0.373	-160.5	3.76	86.4	0.108	45.1	0.382	-74.7
2000	0.373	-168.3	3.42	82.6	0.112	46.5	0.362	-77.9

Table 4 S Parameter ($V_{CE} = 5 \text{ V}$, $I_C = 20 \text{ mA}$, $Z_O = 50 \Omega$)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
200	0.588	-53.1	21.24	144.3	0.0275	66.3	0.826	-31.8
400	0.482	-89.8	15.59	123.6	0.0423	56.6	0.619	-49.8
600	0.419	-115.9	11.75	111.0	0.0507	53.9	0.480	-58.7
800	0.389	-134.1	9.29	102.4	0.0581	54.5	0.395	-63.8
1000	0.366	-149.7	7.64	96.5	0.0652	55.8	0.337	-67.6
1200	0.365	-161.9	6.47	91.4	0.0726	57.3	0.300	-70.1
1400	0.354	-171.4	5.63	97.1	0.0806	58.7	0.274	-72.8
1600	0.356	-179.7	4.98	83.5	0.0877	60.4	0.255	-74.6
1800	0.361	172.7	4.48	79.9	0.0959	61.2	0.242	-77.1
2000	0.365	165.3	4.06	77.0	0.105	62.4	0.232	-79.9